

## ABSTRACT OF THE DISCLOSURE

An etching apparatus is provided, in which a plurality of electrodes are disposed for placing a substrate, high-frequency power sources as many as electrodes are provided, and the electrodes and the high-frequency power sources are connected to each other independently.

5 Among a plurality of electrodes, a high-frequency power applied to an electrode disposed below the central portion of the substrate and a high-frequency power applied to electrodes disposed below corner portions of the substrate are controlled respectively, whereby in-plane uniformity of etching can be enhanced.